

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	36	imai near shigeki.in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 17:41
L2	139	inoguchi near kazuhiko.in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 17:42
L3	30	kobayashi near hikaru.in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 17:42
L4	1	((immersing near5 substrate) with (oxidiz\$3 near3 solution) and (active near3 oxidizing) and (oxide)).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 17:44
L5	1	((immersing near5 substrate) with (oxidiz\$3 near3 solution) and (active near3 oxidizing) and (oxide))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 17:45
L6	27	((immersing near5 substrate) with (oxidiz\$3 near3 solution) and (active) and (oxide))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 17:46
L7	22	6 and @ad<="20050216"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 17:47
L8	59	((immersing near5 substrate) with (oxidiz\$3 near3 solution) and (oxide))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 17:58

L9	48	8 and @ad<="20050216"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 17:58
L10	35	9 and (oxide) with (substrate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 17:58
L11	8	9 and (oxide) with (chemical) with (substrate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 17:59
L12	3	((immers\$3 near5 substrate) with (chemical) with (oxidiz \$3 near3 solution) with (oxide))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 18:04
L13	3	((immers\$3 near5 substrate) with (oxidiz\$3 near3 solution) with (chemical) with (oxide))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 18:05
L14	27	((immers\$3 near5 substrate) with (oxidiz\$3 near3 solution) with (oxide))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 18:05
L15	91	((immers\$3 near5 substrate) with (oxidiz\$3) with (oxide))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 18:05
L16	3	((immers\$3 near5 substrate) with (oxidiz\$3) with (chemical) with (oxide))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 18:05
L17	78	15 and @ad<="20050216"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 18:06

L18	22	17 and ((heat\$3) (electrolyz\$3)) with (oxidiz\$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 18:07
L19	14	18 and concentration	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 18:07
L20	140709	19 and (low-concentration) (low near concentration)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 18:23
L21	3	19 and ((low-concentration) (low near concentration))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 18:23
L22	4	"7156962" "20060051260"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 18:35
L23	1	4 and (low high) with (concentration)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 18:35
L24	1	22 and (low high) with (concentration)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 18:36
L25	2	22 and (voltage)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 18:36
L26	1	25 and silicon	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 18:37

L27	2	22 and (temperature)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 18:39
L28	0	22 and (tgate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 18:45
L29	0	22 and (gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 18:45
L30	1297	(substrate) with (immers\$3) with (concentration)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 18:46
L31	11	(substrate) with (immers\$3) with (oxidizing) with (concentration)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 18:47
L32	5	31 and (low high) with (concentration)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 18:47
L33	19	((substrate) with (immers \$3) with (oxidiz\$3)) and ((low-concentration) (low near concentration)) and ((high-concentration) (high near concentration))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 18:50
L34	17	33 and @ad<="20050216"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 18:50
L35	1	34 and azeotropic	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 18:51

L36	1	34 and azeotrop\$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 18:52
L37	393	azeotropic near concentration	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 18:55
L38	117	(azeotropic near concentration) with (solution liquid)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 18:55
L39	94	38 and @ad<="20050216"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 18:56
L40	20	39 and (lower) with (azeotropic)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 18:56
L41	2176	(solution) with (low near concentration) with (high near concentration)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 19:02
L42	22	(immers\$3) with (solution) with (low near concentration) with (high near concentration)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 19:02
L43	16	42 and @ad<="20050216"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 19:03
L44	520	(oxide) with (monocrystal near silicon)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 19:07

L45	2	(oxide) with (monocrystal near silicon) with (polycrystalline) with (amorphous)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 19:08
L46	2244	(oxidizing near solution) with (acid)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 19:09
L47	36	(oxidizing near solution) with (nitric near acid) with (sulfuric) with (hydrogen near peroxide)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 19:10
L48	31	47 and @ad<="20050216"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 19:11
L49	0	22 and nitrid\$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 19:19
L50	201978	(oxide) with (nitrid\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 19:19
L51	52435	(substrate) with (oxide) with (nitrid\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 19:19
L52	31	(immers\$3) with (solution) with (substrate) with (oxide) with (nitrid\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 19:20
L53	30	52 and @ad<="20050216"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 19:20

L54	0	22 and (tft)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 19:24
L55	0	22 and (transistor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 19:25
L56	173	((tft) (thin near film near transistor)) and (oxidizing) with (solution) with (oxide)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 19:25
L57	1	56 and (substrate) with (atomic near5 density)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 19:26
L58	37	56 and (substrate) with (atomic density)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 19:26
L59	26	58 and @ad<="20050216"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 19:27
L60	7	59 and gate near3 oxide	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 19:27
L61	7	60 and display	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 19:31
L62	1	60 and (display) with (tft)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 19:31

L63	5	60 and (display) with (transistor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 19:32
L64	1	22 and uniform	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 19:35
L65	49	(oxide) with ((nonuniform) (non-uniform)) with (improv\$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 19:36
L66	10	(substrate) with (oxide) with ((nonuniform) (non-uniform)) with (improv\$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 19:36
L67	290	(substrate) with (oxide) with ((nonuniform) (non-uniform))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 19:37
L68	235	67 and @ad<="20050216"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 19:37
L69	18	68 and (immers\$3) with (substrate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 19:37
L70	2	22 and improv\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 19:43
L71	11	(immers\$3) with (oxide) with ((nonuniform) (non-uniform))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 19:45

L72	8	71 and @ad<="20050216"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/31 19:45
S1	2	"20050079703"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/14 22:58

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